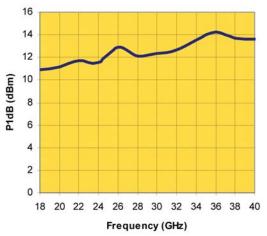


# GaAs HEMT MMIC LOW NOISE AMPLIFIER, 18 - 40 GHz

## On-Wafer P1dB vs. Frequency



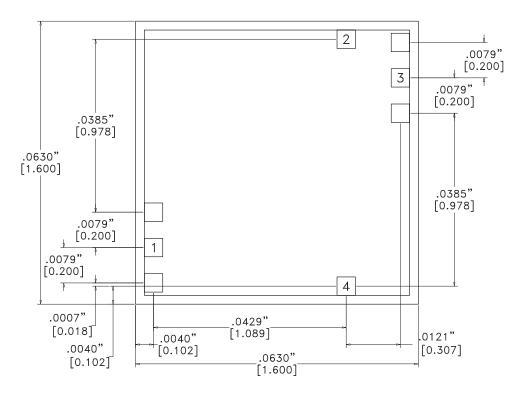
### **Absolute Maximum Ratings**

Drain Bias Voltage	+5.5 Vdc
Drain Bias Current	60 mA
RF Input Power	10 dBm
Thermal Resistance (channel to die bottom)	201.2 °C/W
Channel Temperature	180 °C
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

## **Outline Drawing**



# Die Packaging Information [1]

Standard	Alternate
GP-1 (Gel Pack)	[2]

[1] Refer to the "Packaging Information" section for die packaging dimensions.

[2] For alternate packaging information contact Hittite Microwave Corporation.

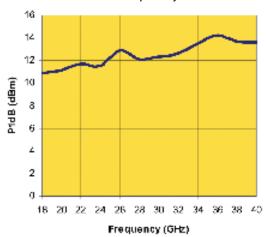
#### NOTES:

- 1. ALL DIMENSIONS ARE IN INCHES [MM].
- 2. TYPICAL BOND PAD IS .004" SQUARE.
- 3. BACKSIDE METALLIZATION: GOLD.
- 4. BACKSIDE METAL IS GROUND.
- 5. BOND PAD METALLIZATION: GOLD.
- 6. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.
- 7. OVERALL DIE SIZE ±.002"



## GaAs HEMT MMIC LOW NOISE AMPLIFIER, 18 - 40 GHz

### On-Wafer P1dB vs. Frequency

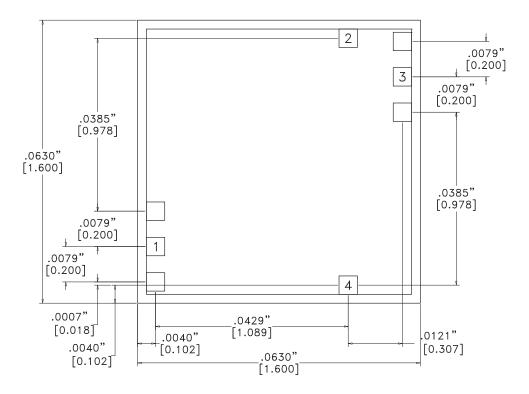


### **Absolute Maximum Ratings**

Drain Bias Voltage	+5.5 Vdc
Drain Bias Current	60 mA
RF Input Power	10 dBm
Thermal Resistance (channel to die bottom)	(124 °C/W)
Channel Temperature	180 °C
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C



### **Outline Drawing**



# Die Packaging Information [1]

Standard	Alternate
GP-1 (Gel Pack)	[2]

[1] Refer to the "Packaging Information" section for die packaging dimensions.
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#### NOTES:

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